

SEMICONDUCTOR TECHNICAL DATA

KTC9013 EPITAXIAL PLANAR NPN TRANSISTOR

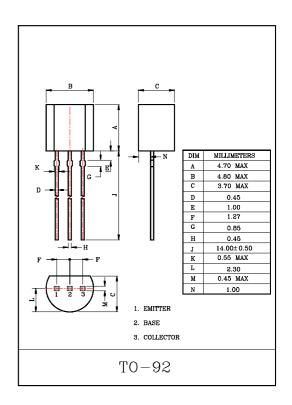
GENERAL PURPOSE APPLICATION. SWITCHING APPLICATION.

FEATURES

- Excellent h_{FE} Linearity.
- · Complementary to KTC9012

MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Collector-Base Voltage	V_{CBO}	40	V	
Collector-Emitter Voltage	V_{CEO}	30	V	
Emitter-Base Voltage	$V_{\rm EBO}$	5	V	
Collector Current	$I_{\rm C}$	500	mA	
Emitter Current	I_{E}	-500	mA	
Collector Power Dissipation	Pc	625	mW	
Junction Temperature	$T_{\rm j}$	150	${\mathbb C}$	
Storage Temperature Range	T_{stg}	-55~150	${\mathbb C}$	



ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB} =35V, I_{E} =0	ı	ı	0.1	μΑ
Emitter Cut-off Current	$I_{ m EBO}$	V_{EB} =5V, I_{C} =0	-	-	0.1	μΑ
DC Current Gain	h _{FE} (Note)	V _{CE} =1V, I _C =50mA	64	-	246	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I_C =100mA, I_B =10mA	ı	0.1	0.25	V
Base-Emitter Voltage	$ m V_{BE}$	I_{C} =100mA, V_{CE} =1 V	_	0.8	1.0	V
Transition Frequency	$ m f_{T}$	V_{CE} =6V, I_{C} =20mA, f=100MHz	140	_	_	MHz
Collector Output Capacitance	C_{ob}	V_{CB} =6V, I_{E} =0, f=1MHz	-	7.0	-	рF

Note: h_{FE} Classification D:64 \sim 91, E:78 \sim 112, F:96 \sim 135, G:118 \sim 166, H:144 \sim 202, I:176 \sim 246